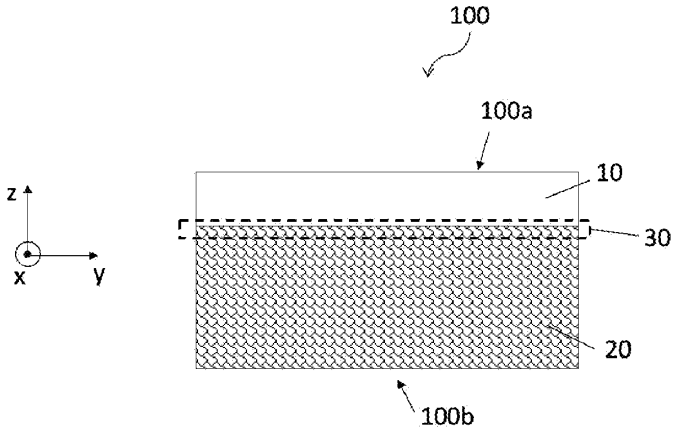
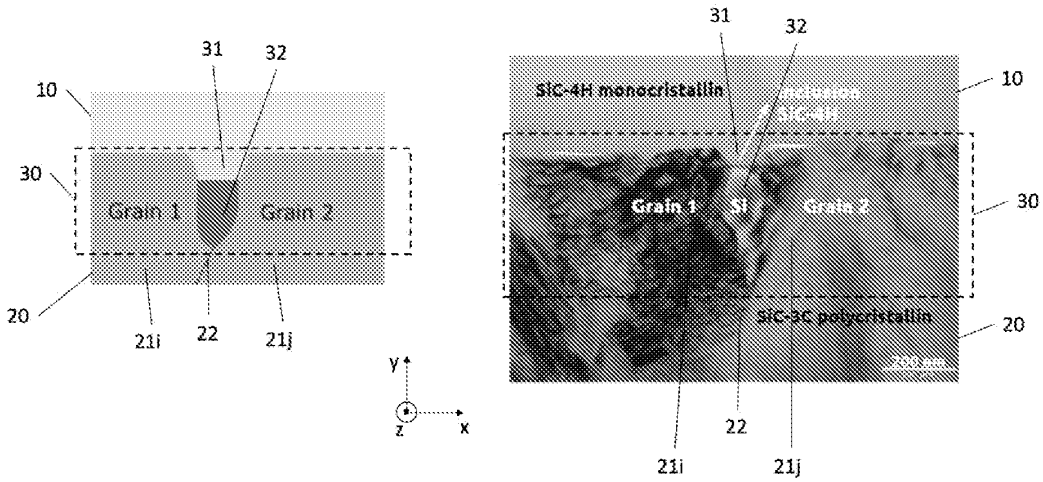
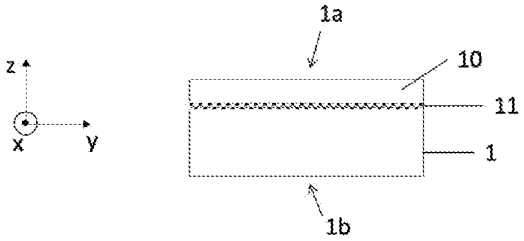
[Fig. 1]



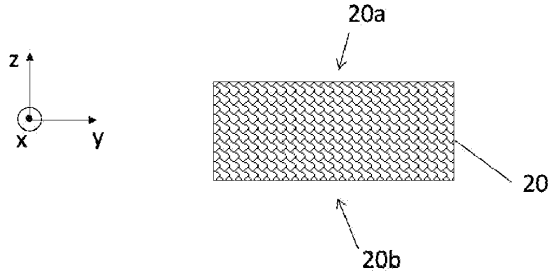
[Fig. 2]



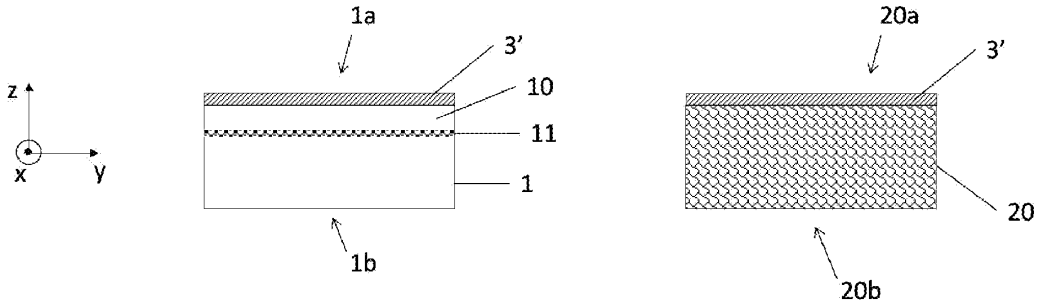
[Fig. 3a]



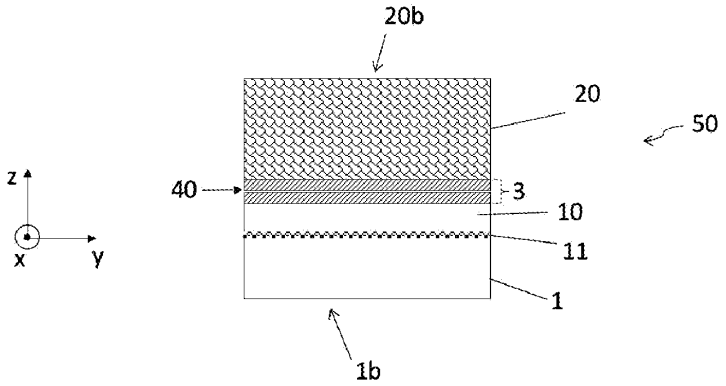
[Fig. 3b]



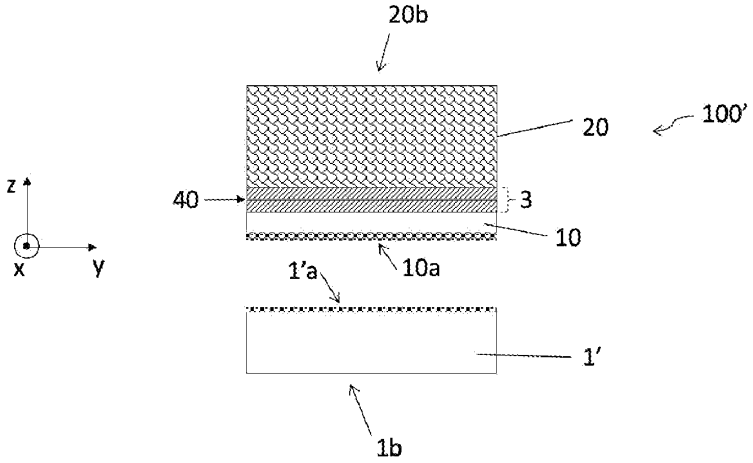
[Fig. 3c]



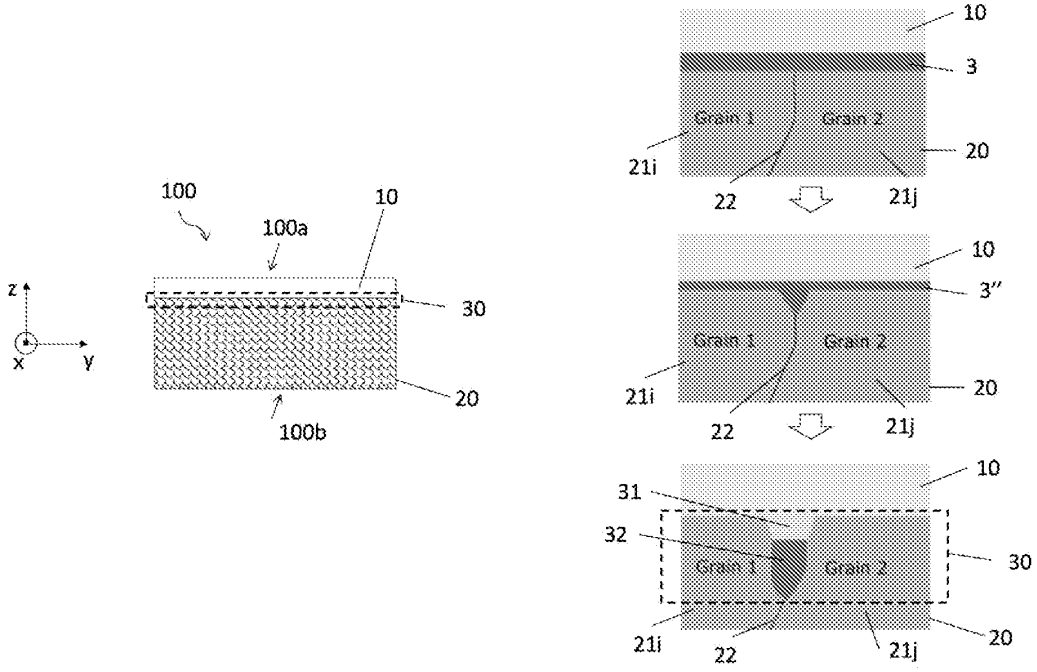
[Fig. 3d]



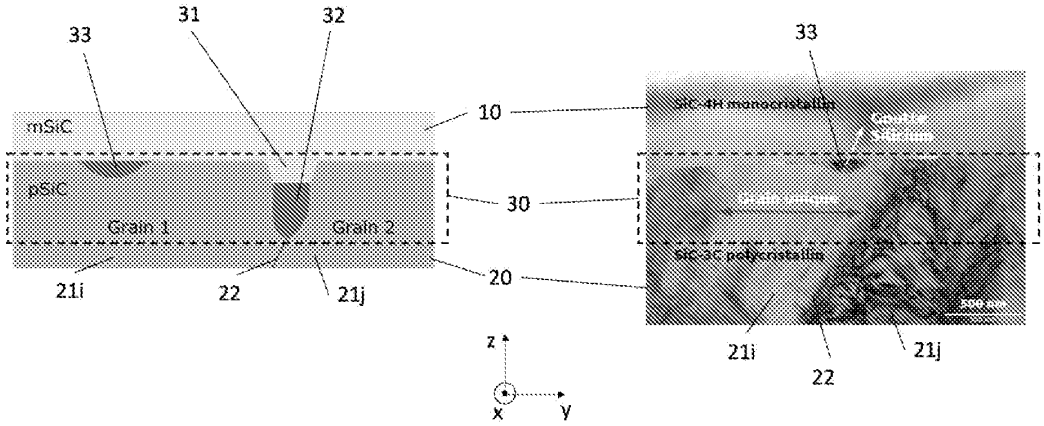
[Fig. 3e]



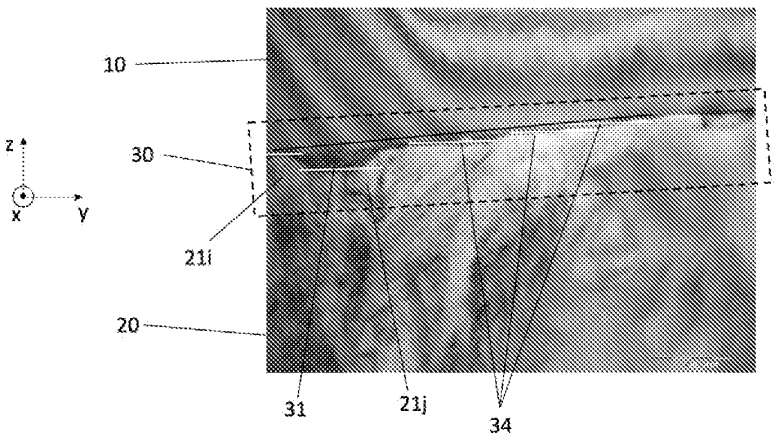
[Fig. 3f]



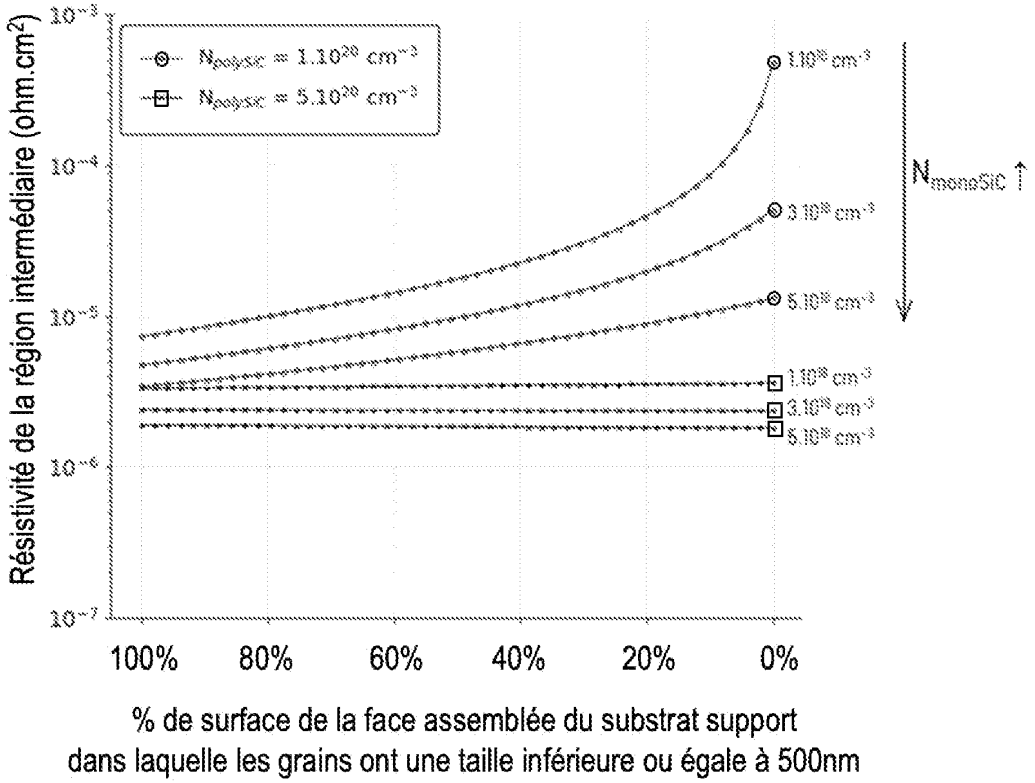
[Fig. 4]



[Fig. 5]



[Fig. 6]


Résistivité de la région intermédiaire (ohm.cm²)
10⁻³
10⁻⁴
10⁻⁵
10⁻⁶
10⁻⁷
N polySiC = 1.10²⁰ cm⁻³
N polySiC = 5.10²⁰ cm⁻³
1.10¹⁹ cm⁻³
3.10¹⁸ cm⁻³
5.10¹⁸ cm⁻³
1.10¹⁸ cm⁻³
3.10¹⁸ cm⁻³
5.10¹⁸ cm⁻³
N monoSiC ↑
100%
80%
60%
40%
20%
0%
% de surface de la face assemblée du substrat support
dans laquelle les grains ont une taille inférieure ou égale à 500nm